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(54) **HOLE-TYPE SADP FOR 2D DRAM CAPACITOR**

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(57) **ABSTRACT**

Memory devices and methods of forming memory devices are described. Methods of forming electronic devices are described where a spacer is formed around each of the bit line contact pillars, the spacer in contact with the spacer of an adjacent bit line contact pillar. A doped layer is then epitaxially grown on the memory stack and bit line is formed on the memory stack. The bit line is self-aligned with the active region.

